

60V N-Channel MOSFET



TO-252 (DPAK)

Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source



PRODUCT SUMMARY

V _{DS} (V)	R_{DSON} (m Ω)	I _D (A)
	65 @ V _{GS} = 10V	10
60	80 @ V _{GS} = 5V	10
	110 @ V _{GS} = 4V	9

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

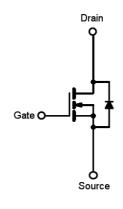
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM10N06CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: "G" denotes for Halogen Free

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I _D	10	Α
Pulsed Drain Current	I _{DM}	50	Α
Continuous Source Current (Diode Conduction) ^{a,b}	I _S	10	Α
Total Power Dissipation @ T _C =25°C	P _{DTOT}	45	W
Operating Junction Temperature	T _J	+150	°C
Operating Junction and Storage Temperature Range	T _J , T _{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\Theta_{JC}$	2.78	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 10$ sec.



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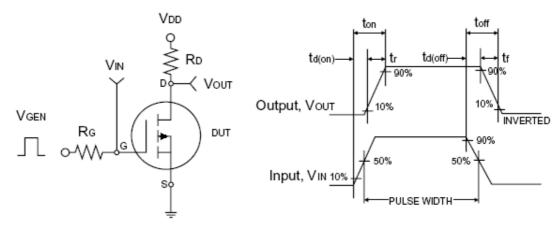


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1		3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			2	μΑ
	$V_{GS} = 10V, I_D = 10A$				65	
Drain-Source On-State Resistance	$V_{GS} = 5V, I_D = 10A$	R _{DS(ON)}			80	mΩ
	$V_{GS} = 4V, I_{D} = 9A$				110	
Forward Transconductance	$V_{DS} = 25V, I_{D} = 6A$	g _{fs}		13		S
Diode Forward Voltage	$I_{S} = 2A, V_{GS} = 0V$	V_{SD}		0.9	1.2	V
Dynamic ²						
Total Gate Charge	$V_{DS} = 30V, I_{D} = 9A,$ $V_{GS} = 4.5V$	Q_g		10.5	16	
Gate-Source Charge		Q_gs		3.5		nC
Gate-Drain Charge		Q_{gd}		4.2		
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		1100		
Output Capacitance		C _{oss}		90		pF
Reverse Transfer Capacitance	1 = 1.0IVII 12	C _{rss}		55		
Switching ^{2,3}						
Turn-On Delay Time	$V_{DD} = 30V, R_{L} = 5.4\Omega,$ $I_{D} = 9A, V_{GEN} = 10V,$ $R_{G} = 1\Omega$	t _{d(on)}		10	15	
Turn-On Rise Time		t _r		15	25	20
Turn-Off Delay Time		$t_{d(off)}$		25	40	nS
Turn-Off Fall Time		t _f		10	15	

Notes 1: Pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ Notes 2: For DESIGN AID ONLY, not subject to production testing.

Notes 3: Switching time is essentially independent of operating temperature.



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Switching Test Circuit

Switchin Waveforms

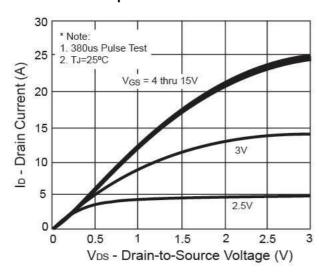


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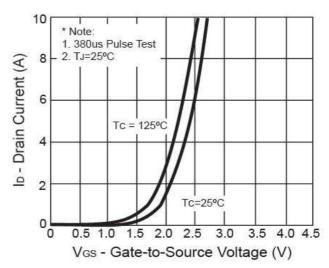


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

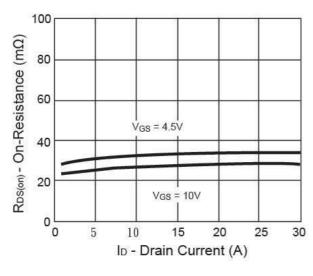
Output Characteristics



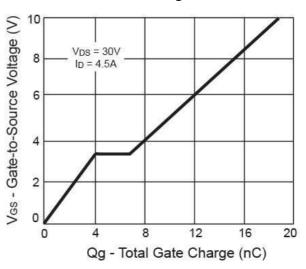
Transfer Characteristics



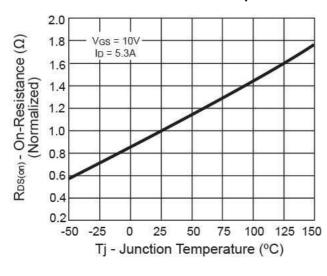
On-Resistance vs. Drain Current



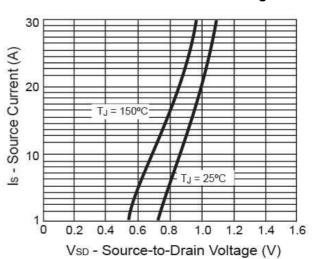
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



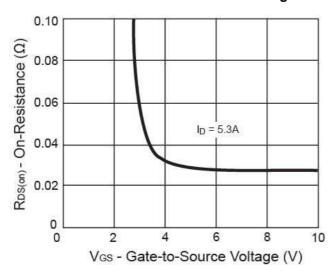


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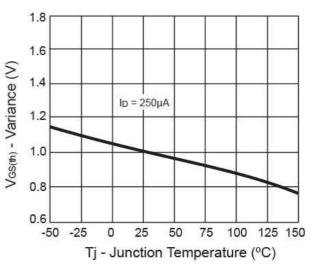


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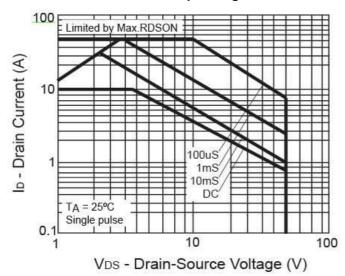
On-Resistance vs. Gate-Source Voltage



Threshold Voltage



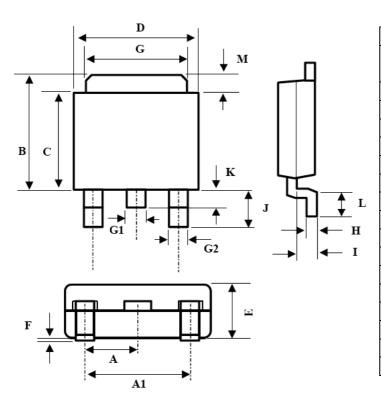
Maximum Safe Operating Area



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TO-252 Mechanical Drawing



TO-252 DIMENSION					
DIM	MILLIMETERS		INCHES		
ואווט	MIN	MAX	MIN	MAX	
Α	2.3BSC		0.09BSC		
A1	4.6E	4.6BSC 0.18BSC		BSC	
В	6.80	7.20	0.268	0.283	
С	5.40	5.60	0.213	0.220	
D	6.40	6.65	0.252	0.262	
Ш	2.20	2.40	0.087	0.094	
F	0.00	0.20	0.000	0.008	
G	5.20	5.40	0.205	0.213	
G1	0.61	0.78	0.024	0.030	
G2	0.51	0.71	0.020	0.028	
Ι	0.35	0.65	0.014	0.026	
Ι	0.90	1.50	0.035	0.059	
J	2.20	2.80	0.087	0.110	
K	0.50	1.10	0.020	0.043	
L	0.90	1.50	0.035	0.059	
М	1.30	1.70	0.051	0.67	

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

 $S = May \quad T = Jun \quad U = Jul \quad V = Aug$

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



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